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novel measurement solutions



3-point Measurement in Solid State Devices: (Novel) Artefacts and How to Avoid Them

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Introduction

There are two common methods to measure the impedance response of only one electrode of a solid-state electrochemical cell; microelectrodes or a three-terminal configuration. In aqueous electrochemistry, three-terminal configurations are widely used, however, implementing this method in solid-state electrochemistry is highly nontrivial. This work summarizes, which method is most suitable for different applications. We show potential error sources and evaluate each of them quantitatively with special emphasis on their impact in thin film electrode measurements. Evaluation is done by means of finite elements analysis (FEA), electric circuit simulations and impedance measurements.

Three potential error sources were identified as particularly crucial factors:

- (i) Asymmetric sample cells
- (ii) Short circuit currents across the reference electrode (RE),
- (iii) Especially for highly resistive electrodes, coupling capacitances between the three electrodes.

These error sources can result in different measurement errors such as additional high frequency semicircles, additional low frequency semicircles, inductive loops and even more critical, erroneous electrode properties without indicating of additional features in the impedance spectrum.

3-Terminal Approaches in Literature

High resistive samples/ High frequencies



a)



Fig. 8 a) Equivalent circuit for a sample with 3 terminal connection, b) The two-terminal equivalent network of a three-terminal electrochemical cell [5]

$$\underline{Z}(\omega)_{3\text{-point}} = \frac{\underline{V}}{I} = \underline{Z}(\omega)_{2\text{-point, equivalent}}$$

This capacitance can be cancelled actively by out shielding the reference electrode coaxial cable. This measure forces the shield of the BNC cable on the same potential like its core, which actively eliminates the capacitance.

- \rightarrow Coupling capacitances may lead to distorted measurement results!
- \rightarrow Important for:
 - \rightarrow Frequency in GHz range
 - \rightarrow High resistive samples





Many attempts were already tried to minimize errors in threeterminal measurements [1-4]. Geometries as shown in Fig. 1 suffer from many shortcomings:

- (i) Very complicated and expensive to fabricate
- (ii) Limited to simple electrodes. E.g. hard to use different deposition methods and to change microstructures of the electrodes
- (iii) Errors strongly depend on geometrical factors and



Error sources:

- 3-point transfer characteristic for high ohmic electrodes and high frequencies
- Reference potential shift caused by WE/CE

a =

K_{electrolyte}

K_{electrode}

thereby on manufacturing limitations such as the hole diameter and depth (I and b in Fig. 1)

Fig. 1 Pellet like 3-terminal configuration [1]

(iv) Very thick electrolytes are necessary \rightarrow electrodes with small resistances can not be measured

Advantages of Wing Geometry:

+ WE/CE alignment easy

symmetrical cells

+ short circuit effect avoided

+ no error for identical WE, CE

+ similar to produce as regular

to achieve

The novel "WING GEOMETRY"

We propose a novel sample geometry, the **Wing Geometry**, which was designed to minimize the measurement errors significantly, but still remains affordable and suitable for different applications.



Fig. 9 a) Wing geometry with b) Current distribution ($\omega \rightarrow \infty$)

Fig. 10 Measurement errors for worst case scenario (low-ressistive electrodes and identical relaxation times) with given geometry and changing protrusion height (blue arrow in Fig. 11), protrusion depth = **0,5 mm (red arrow in Fig. 11)**, electrolyte thickness = 1 mm. This intrinsic error source can be minimized by minimizing a and b.



Practical solutions for the "WING GEOMETRY"



 $\omega_{WE} = \omega_{CE}$ (error not visible) Red Orange $\omega_{WE} = 100 \times \omega_{CE}$ (low frequency error) **Green** $\omega_{WE} = \omega_{CE}$ (symmetric, ideal measurement)

indicates the effect from reference potential shift as shown in Fig.3 & 5. b) & c) High frequency error. Simulated impedance spectra with $\omega_{WF} = \omega$ _{CE}/100 resulting in a measurement error in the high frequency range. Fig. 12b and 12c represent spectra from WE and CE respectively.

Fig.12b $\omega_{WF} = \omega_{CF}/100$ (high frequency error)

Cross check results by measuring CE vs RE WE, CE switch at impedance $\omega =$ spectrometer to get an idea of WE/CE RC asymmetry.

References	Abbreviations	Acknowledgements
 J. Winkler et al., Journal of The Electrochemical Society 145.4 (1998), pp. 1184 1192 S. Adler, Journal of The Electrochemical Society 149.5 (2002) E166-E172 M. Nagata, et al. Solid State Ionics 67.3-4 (1994), pp. 215224 G. Hsieh et al., Solid State Ionics 96 (1997), pp. 153172 S. Fletcher, Electrochemistry Communications 3.12 (2001), pp. 692-696 	WEWorking electrodeREReference electrodeCECounter electrode R_{pol} Polarization resistance C_{chem} Chemical capacitance	The authors would like to acknowledge Austrian Science Fund (FWF) (project: SFB-F4502-N16 FOXSI) FOXSI FunctionalOxide Surfaces and Interfaces